



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240416US0DIV		SERIAL NO. 10/618,085		
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Masakazu KANECHIKA, et al.				
				FILING DATE July 14, 2003		GROUP 2813		
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	AA							
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO			
TN	AO	JP8-306752	11-22-96	JAPAN (with English Abstract)	ABST.			
TN	AP	JP7-118100	05-09-95	JAPAN (with English Abstract)	ABST.			
TN	AQ	JP8-203863	08-09-96	JAPAN (with English Abstract)	ABST.			
TN	AR	JP9-232482	09-05-97	JAPAN (with English Abstract)	ABST.			
	AS							
	AT							
	AU							
	AV							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)								
TN	AW	Hayakawa et al; "Mechanism of Residue Formation in Silicon Trench Etching Using a Bromine-Based Plasma," Jpn. J. Appl. Phys., Vol. 37 (1998) pp. 5-9.						
	AX							
	AY							
	AZ					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner T. NGUYEN					Date Considered 10/27/04			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								